(Tc = 25°C unless otherwise specified)

| | | | | | |
|---|---|---|---|---|---|
| $V_{DS,max}$ | Drain source voltage | 1200 | V | $V_{GS}$ = 0V, $I_D$ = 100μA | |
| $V_{GS,max}$ | Gate source voltage | -8 /+22 | V | Absolute maximum values | Note1 |
| $V_{GSpulse}$ | Gate-source voltage,max. transient voltage | -10 /+25 | V | $t_p \leq 0.5\mu s$, D 0.01 | |
| $V_{GSop}$ | Gate source voltage | -4 /+15~18 | V | Recommended operational values | |
| $I_D$ | Cn?de | | | | |

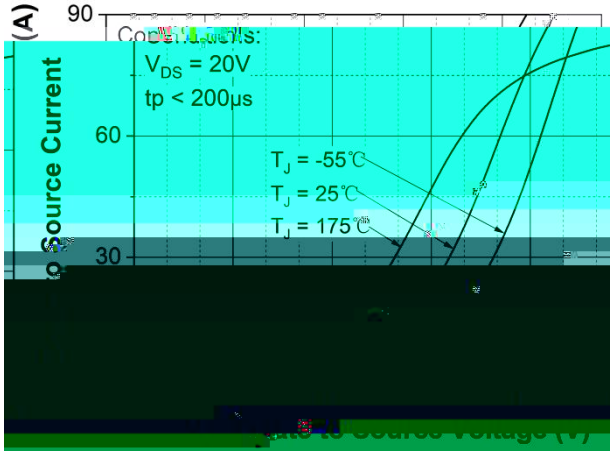



Figure 7. Transfer characteristic for various junction temperatures

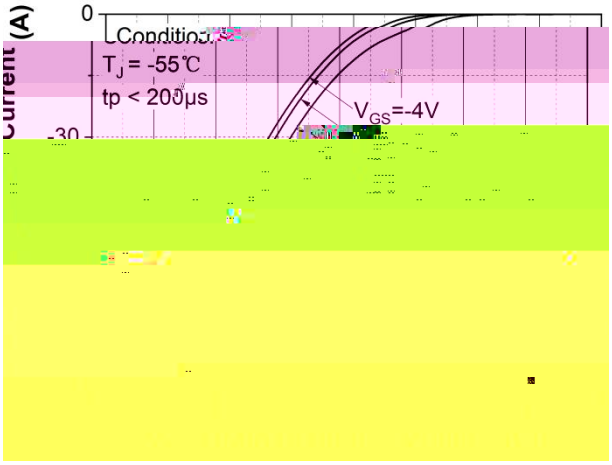



Figure 8. Body diode characteristic at $T_J$ = -55 ºC

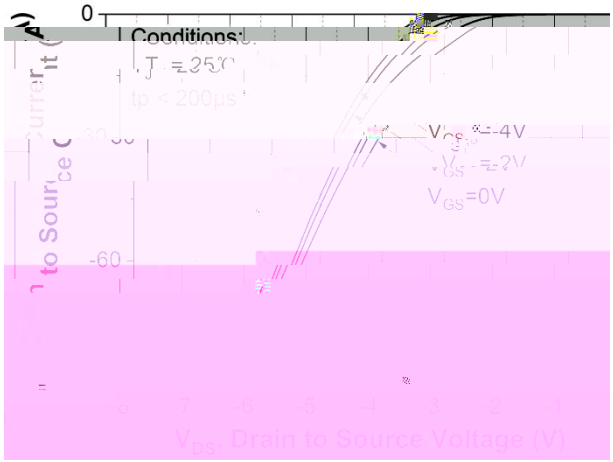



Figure 9. Body diode characteristic at $T_J$ = 25 ºC

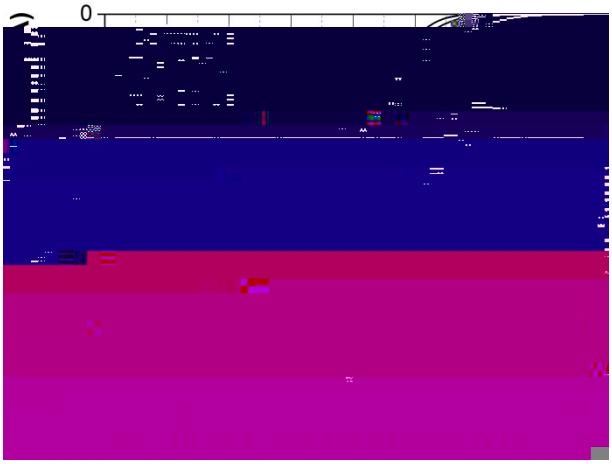



Figure 10. Body diode characteristic at $T_J$ = 175ºC

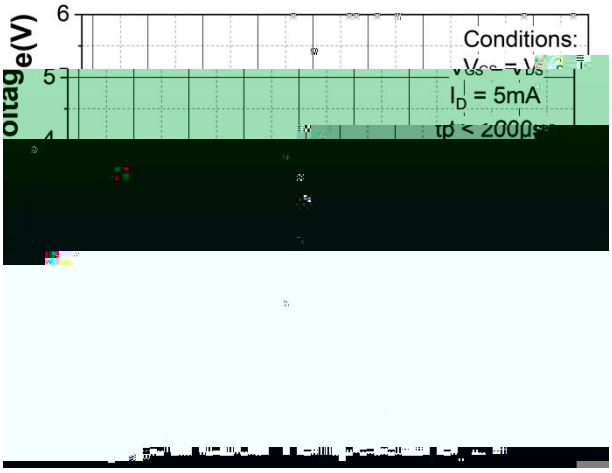



Figure 11. Threshold voltage vs. temperature

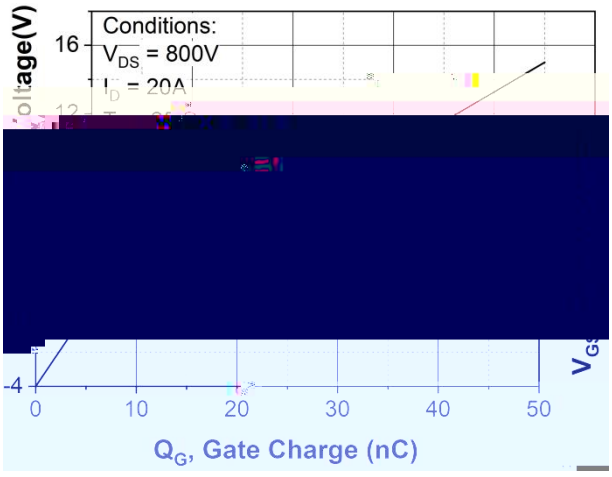



Figure 12. Gate charge characteristic

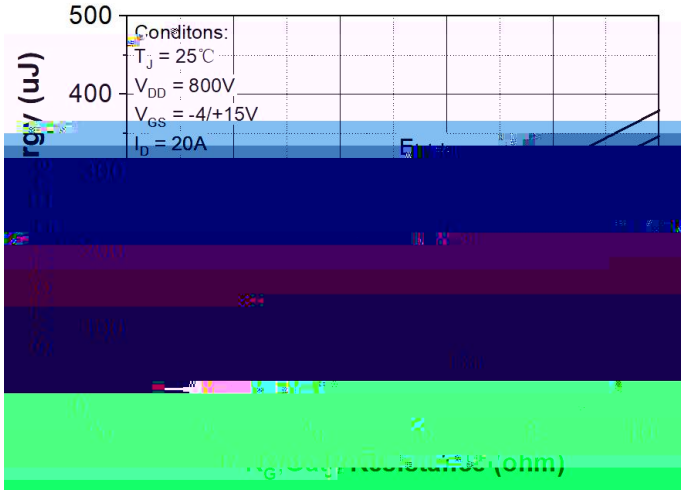



Figure 25. Clamped inductive switching energy vs. $R_G$(ext)

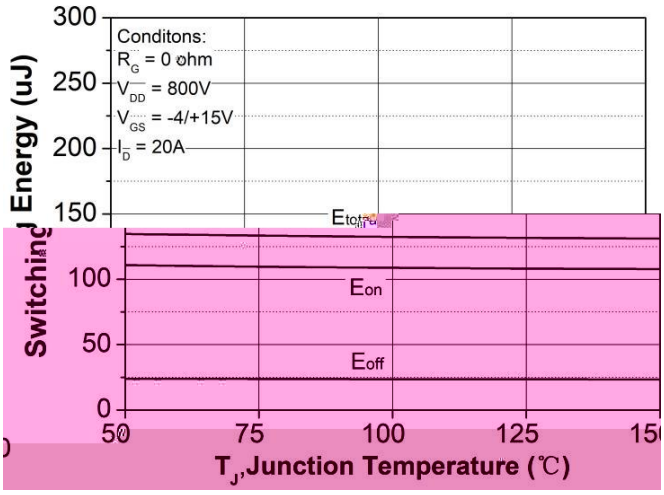



Figure 26. Reverse characteristics vs.$T_J$

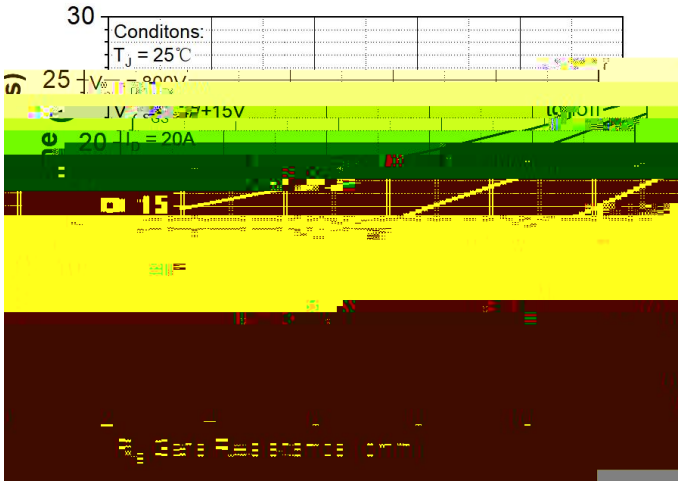



Figure 27. Switching times vs. $R_G$ (ext)

( TO-263-7L-A )

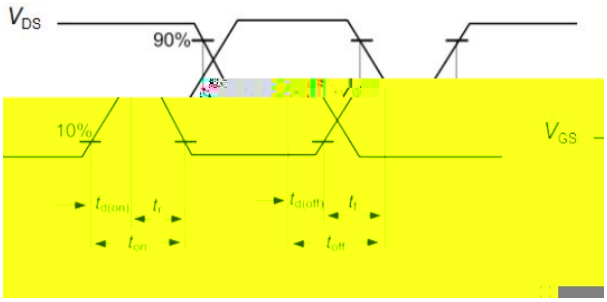



Figure A. Definition of switching times

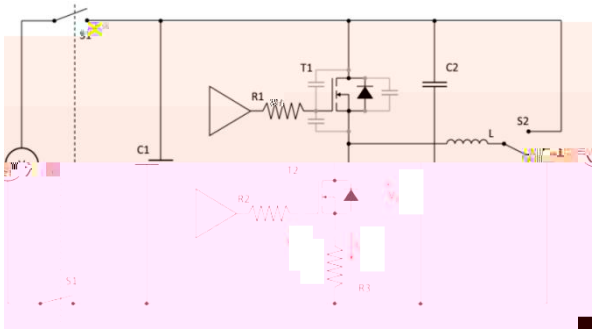



Figure B. Dynamic test circuit

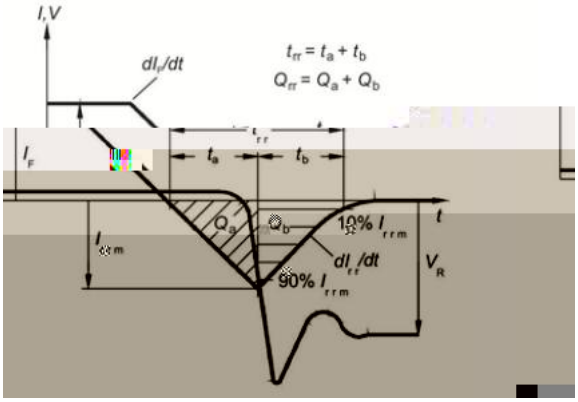



Figure C. Definition of body diode switching characteristics

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|---|---|---|---|
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| | | —— | —— |
| | | —— | —— |
| | | —— | —— |
| | | —— | —— |
| | | | —— |

1.
The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/ EC (RoHS2), as implemented January 2, 2013.

2.
REACh

6. Due to technical requirements products may contain dangerous substances.